

## PSMN2R0-30YLD

# N-channel 30 V, 2.0 m $\Omega$ logic level MOSFET in LFPAK56 using NextPowerS3 Technology

11 December 2014

Product data sheet

### 1. General description

Logic level gate drive N-channel enhancement mode MOSFET in LFPAK56 package. NextPowerS3 portfolio utilising Nexperia's unique "SchottkyPlus" technology delivers high efficiency, low spiking performance usually associated with MOSFETs with an integrated Schottky or Schottky-like diode but without problematic high leakage current. NextPowerS3 is particularly suited to high efficiency applications at high switching frequencies.

### 2. Features and benefits

- Ultra low Q<sub>G</sub>, Q<sub>GD</sub> and Q<sub>OSS</sub> for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery; s-factor > 1
- Low spiking and ringing for low EMI designs
- Unique "SchottkyPlus" technology; Schottky-like performance with < 1 μA leakage at 25 °C
- Optimised for 4.5 V gate drive
- Low parasitic inductance and resistance
- High reliability clip bonded and solder die attach Power SO8 package; no glue, no wire bonds, gualified to 175 °C
- Wave solderable; exposed leads for optimal visual solder inspection

### 3. Applications

- On-board DC-to-DC solutions for server and telecommunications
- Secondary-side synchronous rectification in telecommunication applications
- Voltage regulator modules (VRM)
- Point-of-Load (POL) modules
- Power delivery for V-core, ASIC, DDR, GPU, VGA and system components
- Brushed and brushless motor control

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	30	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 2</u>	[1]	-	-	100	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	142	W



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Tj	junction temperature		-55	-	175	°C
Static charac	teristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 4.5 V; $I_{D}$ = 25 A; $T_{j}$ = 25 °C; Fig. 10	-	2.1	2.5	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 10	-	1.61	2	mΩ
Dynamic cha	racteristics	1				
$Q_{GD}$	gate-drain charge	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; Fig. 12; Fig. 13	-	6.3	-	nC
Q <sub>G(tot)</sub>	total gate charge	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; Fig. 12; Fig. 13	-	21.8	-	nC
Source-drain	diode					
S	softness factor	$I_S$ = 25 A; $V_{GS}$ = 0 V; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{DS}$ = 15 V; <u>Fig. 16</u>	-	1.02	-	

<sup>[1]</sup> Continuous current is limited by package.

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source	<u> </u>	
3	S	source	[d	G T A
4	G	gate	وووو	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

### 6. Ordering information

Table 3. Ordering information

Type number	Package	ackage					
	Name	Description	Version				
PSMN2R0-30YLD	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669				

### 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PSMN2R0-30YLD	2D030L

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	30	V
$V_{DGR}$	drain-gate voltage	25 °C ≤ $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ		-	30	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	142	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	100	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>	[1]	-	100	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 ^{\circ}C$ ; Fig. 3		-	793	Α
T <sub>stg</sub>	storage temperature			-55	175	°C
T <sub>j</sub>	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ		1000	-	V
Source-drain	diode					,
Is	source current	T <sub>mb</sub> = 25 °C	[1]	-	100	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	793	Α
Avalanche ru	ggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 25 A; $V_{sup} \le$ 30 V; $R_{GS}$ = 50 Ω; unclamped; $t_p$ = 815 μs	[2]	-	397	mJ

<sup>[1]</sup> Continuous current is limited by package.

<sup>[2]</sup> Protected by 100% test

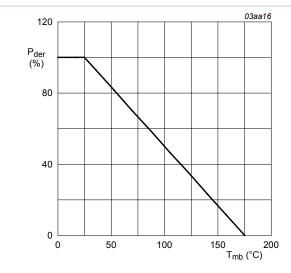
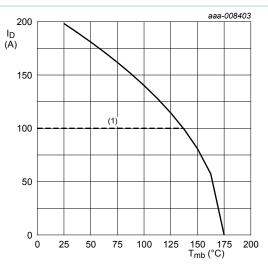


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$



(1) Capped at 100A due to package

Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 10V$$

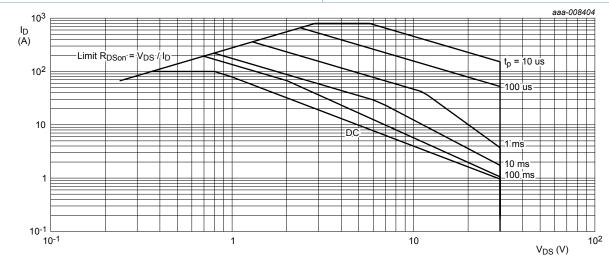


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$$T_{mb} = 25$$
°C;  $I_{DM}$  is a single pulse

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 4	-	0.92	1.06	K/W

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	<u>Fig. 5</u>	-	50	-	K/W
	from junction to ambient	Fig. 6	-	125	-	K/W

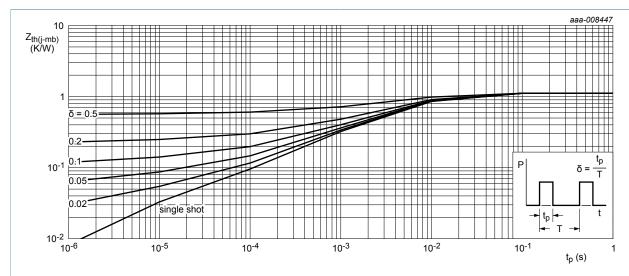


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

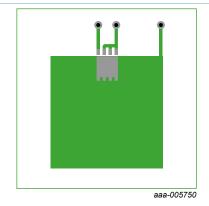


Fig. 5. PCB layout for thermal resistance junction to ambient 1" square pad; FR4 Board; 2oz copper

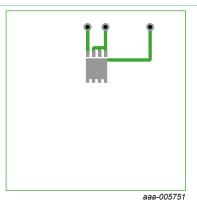


Fig. 6. PCB layout for thermal resistance junction to ambient minimum footprint; FR4 Board; 2oz copper

### 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static characteristics							
V <sub>(BR)DSS</sub>		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$		30	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$		27	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$		1.2	1.7	2.2	V

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T <sub>j</sub> ≤ 150 °C	-	-4.4	-	mV/K
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 24 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>DS</sub> = 24 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	1.7	-	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 10	-	2.1	2.5	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 150 °C; Fig. 11; Fig. 10	-	-	4.2	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 10	-	1.61	2	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 150 °C; Fig. 11; Fig. 10	-	-	3.3	mΩ
$R_G$	gate resistance	f = 1 MHz	-	0.9	-	Ω
Dynamic cha	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 10 V; Fig. 12; Fig. 13	-	46	-	nC
		I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 4.5 V; Fig. 12; Fig. 13	-	21.8	-	nC
		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V	-	41.5	-	nC
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 4.5 V;	-	6.8	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	Fig. 12; Fig. 13	-	4.5	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	2.3	-	nC
$Q_{GD}$	gate-drain charge		-	6.3	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; <u>Fig. 12</u> ; <u>Fig. 13</u>	-	2.5	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	2969	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 14</u>	-	1477	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	206	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 15 V; $R_L$ = 0.6 $\Omega$ ; $V_{GS}$ = 4.5 V;	-	19	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	31	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	24	-	ns
t <sub>f</sub>	fall time		-	19	-	ns

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q <sub>oss</sub>	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$		-	31.6	-	nC
Source-dra	nin diode						,
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 15$		-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	37.5	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 15 V; <u>Fig. 16</u>	[1]	-	32	-	nC
t <sub>a</sub>	reverse recovery rise time			-	18.6	-	ns
t <sub>b</sub>	reverse recovery fall time			-	18.9	-	ns
S	softness factor			-	1.02	-	

#### [1] includes capacitive recovery

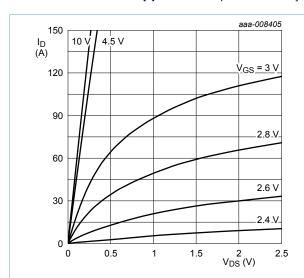


Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values



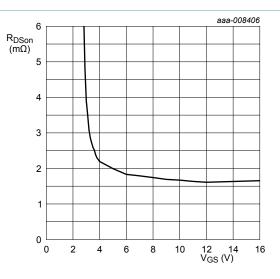


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

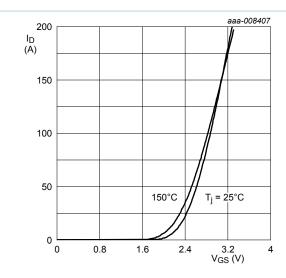


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

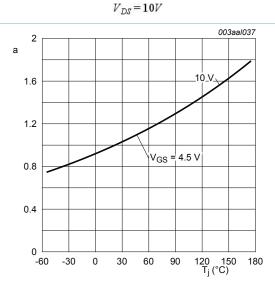


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

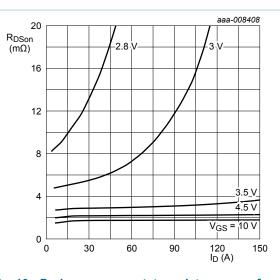


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

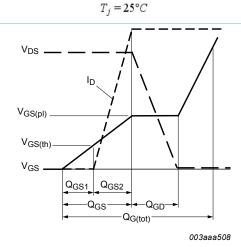


Fig. 12. Gate charge waveform definitions

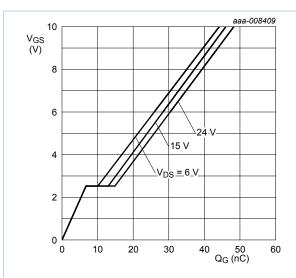


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

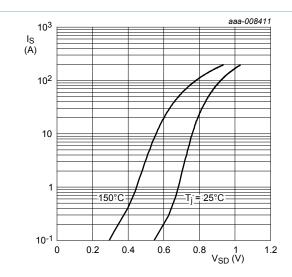


Fig. 15. Source current as a function of source-drain voltage; typical values

$$V_{GS} = 0V$$

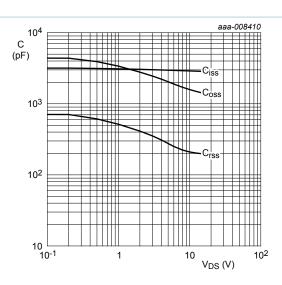


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; \ f = \mathbf{1}MHz$$

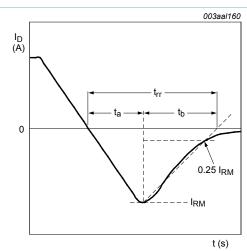
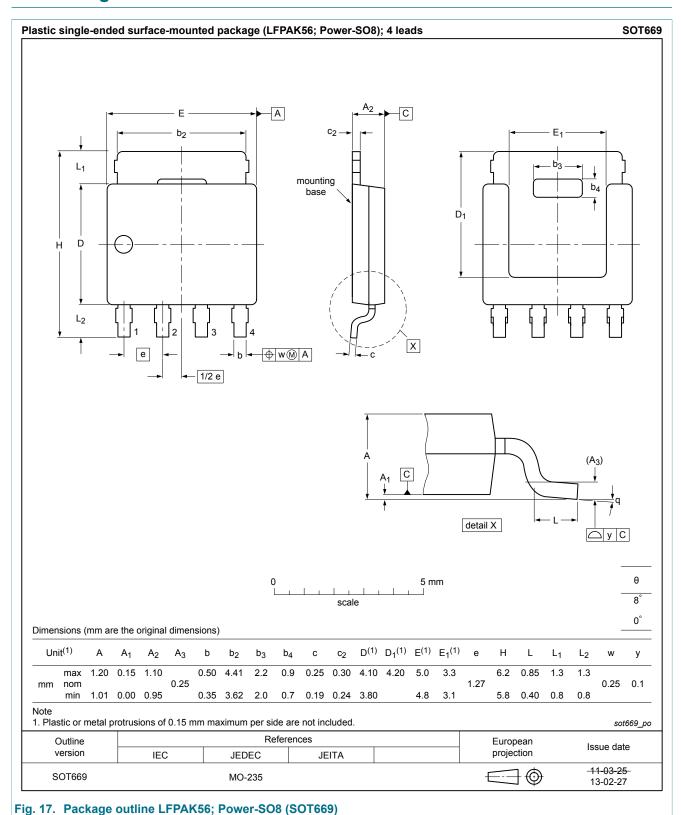


Fig. 16. Reverse recovery timing definition

### 11. Package outline



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